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PATENT

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of Gregory Michael Wilson et al.
Serial No. 09/608,302
Filed June 30, 2000
Confirmation No. 9819
For A METHOD AND APPARATUS FOR FORMING A
SILICON WAFER WITH A DENUDED ZONE
Examiner Robert M. Kunemund

Art Unit 1765

February 28, 2002

AMENDMENT A

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TO THE ASSISTANT COMMISSIONER FOR PATENTS,

SIR:

In response to the Office action dated September 28, 2001, please enter the following amendments into the record of this case:

IN THE CLAIMS:

Please replace claim 1 with the following:

5A 1. (amended) A method of producing a denuded zone in a semiconductor wafer in a housing having a source of heat, a susceptor, a wafer support and a Bernoulli wand, said method including:

heating a semiconductor wafer with opposite major surfaces in a housing to an elevated temperature of at least about 1175°C with a heat source, said semiconductor being supported by a support in the housing during said heating;

ceasing said heating and moving said semiconductor out of conductive heat transfer relation with the support with the Bernoulli wand; and

10 cooling said heated wafer in the housing while holding said wafer out of conductive heat transfer relationship with the support at a rate of at least 10°C/sec until the wafer reaches a temperature of less than about 850°C thereby forming a template for oxygen precipitation in the wafer.

Please amend claim 2 with the following:

2. (amended) A method as set forth in claim 1 wherein the process additionally comprises the step of placing the wafer in a chamber and applying an epitaxial coating